

## **isc Silicon NPN Power Transistor**

## 2SD1763A

### DESCRIPTION

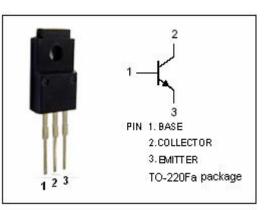
- High Collector-Emitter Breakdown Voltage-: V<sub>(BR)CEO</sub>= 160V(Min.)
- · Good Linearity of hFE
- Complement to Type 2SB1186A
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

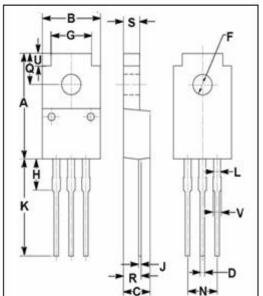
#### **APPLICATIONS**

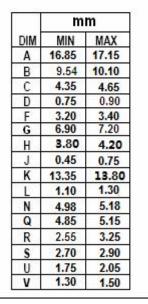
- Power amplifier applications.
- Driver stage amplifier applications.

SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>CBO</sub>	Collector-Base Voltage	160	V	
V <sub>CEO</sub>	Collector-Emitter Voltage	160	V	
$V_{\text{EBO}}$	Emitter-Base Voltage	5	V	
Ι <sub>C</sub>	Collector Current-Continuous	1.5	А	
Ісм	Collector Current-Peak	3	A	
Pc	Collector Power Dissipation @ Ta=25°C	2	w	
	Collector Power Dissipation @ $T_C$ =25°C	20		
TJ	Junction Temperature	150	°C	
T <sub>stg</sub>	Storage Temperature Range	-55~150	°C	

### ABSOLUTE MAXIMUM RATINGS(Ta=25°C)







isc website: www.iscsemi.com



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### **ELECTRICAL CHARACTERISTICS**

### $T_{c}\text{=}25^{\circ}\!\!\!\mathrm{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 1mA; I <sub>B</sub> = 0	160			V
V <sub>(BR)</sub> CBO	Collector-Base Breakdown Voltage	Ic= 50 μ A; I <sub>E</sub> = 0	160			V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 50 μ A; I <sub>C</sub> = 0	5			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 1A; I <sub>B</sub> = 0.1A			2.0	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 1A; I <sub>B</sub> = 0.1A			1.5	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 120V; I <sub>E</sub> = 0			1	μA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 4V; I <sub>C</sub> = 0			1	μA
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 0.1A; V <sub>CE</sub> = 5V	60		200	
Сов	Output Capacitance	I <sub>E</sub> = 0; V <sub>CB</sub> = 10V; f <sub>test</sub> =1MHz		20		pF
f⊤	Current-Gain—Bandwidth Product	I <sub>E</sub> = -0.1A; V <sub>CE</sub> = 5V; f <sub>test</sub> = 30MHz		80		MHz

### h<sub>FE</sub> Classifications

D	E		
60-120	100-200		

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